

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

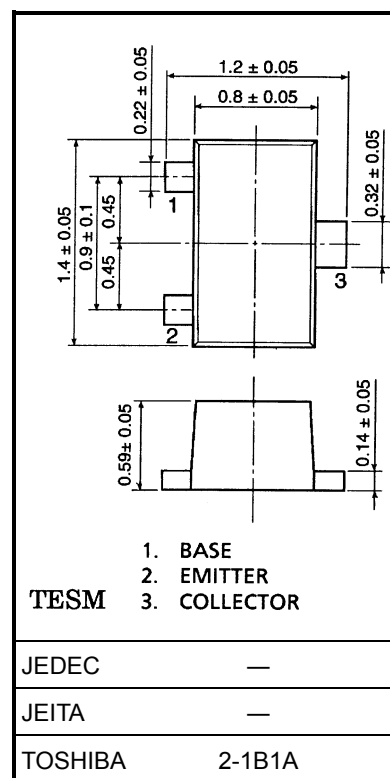
## 2SC5111FT

For VCO Application

Unit: mm

## Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	20	V
Collector-emitter voltage	$V_{CEO}$	10	V
Emitter-base voltage	$V_{EBO}$	3	V
Base current	$I_B$	30	mA
Collector current	$I_C$	60	mA
Collector power dissipation	$P_C$	100	mW
Junction temperature	$T_j$	125	°C
Storage temperature range	$T_{stg}$	-55~125	°C



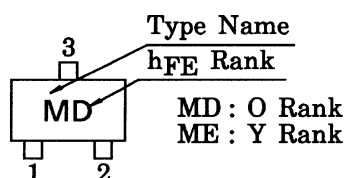
Weight: 0.0022 g (typ.)

## Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = 10\text{ V}, I_E = 0$	—	—	0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 1\text{ V}, I_C = 0$	—	—	0.1	$\mu\text{A}$
DC current gain	$h_{FE}$ (Note 1)	$V_{CE} = 5\text{ V}, I_C = 5\text{ mA}$	80	—	240	
Transition frequency	$f_T$	$V_{CE} = 5\text{ V}, I_C = 5\text{ mA}$	3	5	—	GHz
Insertion gain	$ S_{21e} ^2$	$V_{CE} = 5\text{ V}, I_C = 5\text{ mA}, f = 1\text{ GHz}$	6	10	—	dB
Output capacitance	$C_{ob}$	$V_{CB} = 5\text{ V}, I_E = 0, f = 1\text{ MHz}$ (Note 2)	—	0.9	—	pF
Reverse transfer capacitance	$C_{re}$		—	0.7	1.1	pF
Collector-base time constant	$C_C \cdot r_{bb'}$	$V_{CB} = 5\text{ V}, I_C = 3\text{ mA}, f = 30\text{ MHz}$	—	6	11	ps

Note 1:  $h_{FE}$  classification O: 80~160, Y: 120~240Note 2:  $C_{re}$  is measured by 3 terminal method with capacitance bridge.

## Marking



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